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Electronic Structure of Surfaces in GeSe Layered Semiconductor

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Abstract: Green´s function method in bases sets of Linear Combinations of Atomic Orbitals (LCAO) is used to calculate the electronic structure of the (010) surface of GeSe semiconductor. The energy states in energy gaps, their origin, orbital content, resonances and local changes in the density of states due to the surface are discussed.

Key Words: Green´s function methods, Defects, Single crystal surfaces, Surface defects.

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